

## Amendments to the Specification

Amend paragraph 21 to read as follows:

Referring to Fig. 2, at least one oxygen containing vapor precursor is fed to conductive first metal electrode layer 16 below the selected oxidation temperature under conditions effective to form a first portion oxide material 18 over conductive metal first electrode layer 16. Accordingly with the above exemplary materials, an exemplary preferred oxidation temperature below which the at least one vapor precursor is flowed is 300°C, by way of example only 290°C. First portion 18 will comprise a portion of a capacitor dielectric region 20, as will be apparent from the continuing discussion. By way of example only, an exemplary preferred material is aluminum oxide. Also as shown, first portion 18 is preferably formed “on” (meaning in direct physical contact with) conductive metal first electrode layer 16. Most preferably, first portion oxide material 18 is formed without any measurable oxidation occurring of metal first electrode ~~layer 14~~ layer 16, although some oxidation thereof is not precluded in the broadest considered aspects of the invention, as claimed. By way of example only, the conditions might include chemical vapor deposition (for example feeding multiple vapor precursors simultaneously to the substrate),

atomic layer deposition, yet-to-be developed methods and/or any combination thereof. For example with respect to atomic layer deposition, the conditions might include previous formation of a monolayer to which one or more multiple oxygen containing precursor feeds occur.

Amend paragraph 25 to read as follows:

By way of example only, exemplary capacitor dielectric materials include any one or combination of HfO<sub>2</sub>, Ta<sub>2</sub>O<sub>5</sub>, Y<sub>2</sub>O<sub>3</sub>, ZrO<sub>2</sub>, HfSiO<sub>4</sub>, ZrSiO<sub>4</sub> and YSiO<sub>4</sub>. ~~Further non-oxygen~~ Further, non-oxygen containing capacitor dielectric materials might be employed alternately or in addition to oxygen containing capacitor dielectric materials. Where an oxide is to be formed, exemplary oxidizers include O<sub>2</sub>, O<sub>3</sub>, H<sub>2</sub>O, NO<sub>2</sub>, NO and any alcohols (including polyols). Exemplary precursors include metallorganic precursors, for example tertbutylaluminum alkoxide, triethylaluminum, trimethylaluminum, tetrakisdimethylamido hafnium, pentathoxy tantalum, ~~n~~butyl n-butyl cyclopentadienyl yttrium, and other metal alkyls or metal alkoxides.